

FH6880A

N-Channel Trench Power MOSFET

General Description

The FH6880A is N-channel MOS Field Effect Transistor designed for high current switching applications. Rugged EAS capability and ultra low $R_{DS(ON)}$ is suitable for PWM, load switching applications.

Features

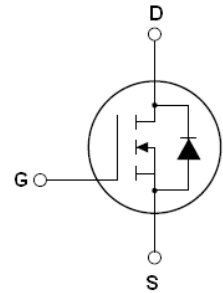
- $V_{DS}=60V$; $I_D=80A$
 $R_{DS(ON)} < 15m\Omega$ @ $V_{GS}=10V$
- Ultra Low On-Resistance
- High UIS and UIS 100% Test

Application

- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply



To-263 Top View



Schematic Diagram

$V_{DS} = 60 V$

$I_D = 80A$

$R_{DS(ON)} = 11m\Omega$

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FH6880A	FH6880A	TO-263	-	-	-

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	60	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 25	V
$I_{D(DC)}$	Drain Current (DC) at $T_c=25^\circ C$	80	A
$I_{D(DC)}$	Drain Current (DC) at $T_c=100^\circ C$	45	A
$I_{DM(pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	180	A
dv/dt	Peak Diode Recovery Voltage	11	V/ns
P_D	Maximum Power Dissipation($T_c=25^\circ C$)	68	W
	Derating Factor	0.45	W/°C
E_{AS}	Single Pulse Avalanche Energy (Note 2)	182	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	°C

Notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. EAS condition: $T_J=25^\circ C, V_{DD}=30V, V_G=10V, R_g=25 \Omega$

Table 2. Thermal Characteristic

Symbol	Parameter	Value	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	---	2.2	$^{\circ}C/W$

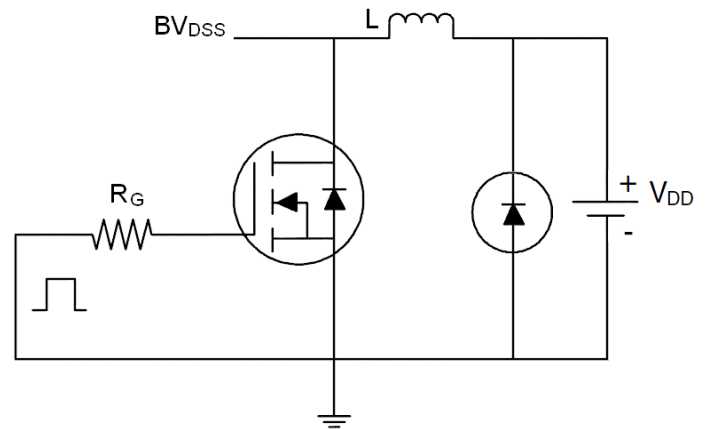
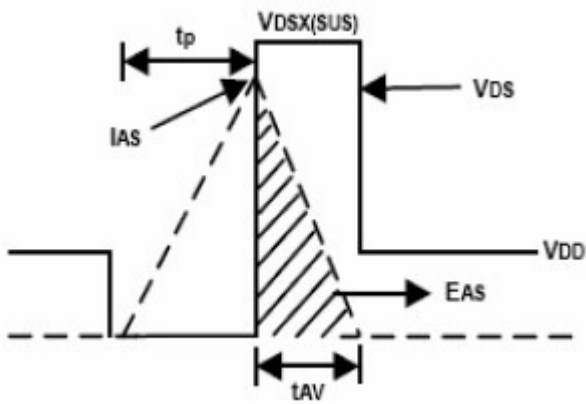
Table 3. Electrical Characteristics (TA=25 $^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60			V
I_{DSS}	Zero Gate Voltage Drain Current($T_c=25^{\circ}C$)	$V_{DS}=60V, V_{GS}=0V$			1	μA
I_{DSS}	Zero Gate Voltage Drain Current($T_c=125^{\circ}C$)	$V_{DS}=60V, V_{GS}=0V$			5	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=10V, I_D=40A$		11	15	m Ω
Dynamic Characteristics						
g_{FS}	Forward Transconductance	$V_{DS}=10V, I_D=15A$	18			S
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$		1717		pF
C_{oss}	Output Capacitance			180		pF
C_{rss}	Reverse Transfer Capacitance			140		pF
Q_g	Total Gate Charge	$V_{DS}=30V, I_D=15A,$ $V_{GS}=10V$		50		nC
Q_{gs}	Gate-Source Charge			12		nC
Q_{gd}	Gate-Drain Charge			23		nC
Switching Times						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=30V, I_D=2A, R_L=2.5\Omega$ $V_{GS}=10V, R_G=3\Omega$		15		nS
t_r	Turn-on Rise Time			25		nS
$t_{d(off)}$	Turn-Off Delay Time			50		nS
t_f	Turn-Off Fall Time			23		nS
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current(Body Diode)			80		A
I_{SDM}	Pulsed Source-Drain Current(Body Diode)			180		A
V_{SD}	Forward On Voltage(Note 1)	$T_J=25^{\circ}C, I_{SD}=1A, V_{GS}=0V$		0.85	0.99	V
t_{rr}	Reverse Recovery Time(Note 1)	$T_J=25^{\circ}C, I_F=15A$ $di/dt=100A/\mu s$		24		nS
Q_{rr}	Reverse Recovery Charge(Note 1)			30		nC
t_{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible(turn-on is dominated by L_S+L_D)				

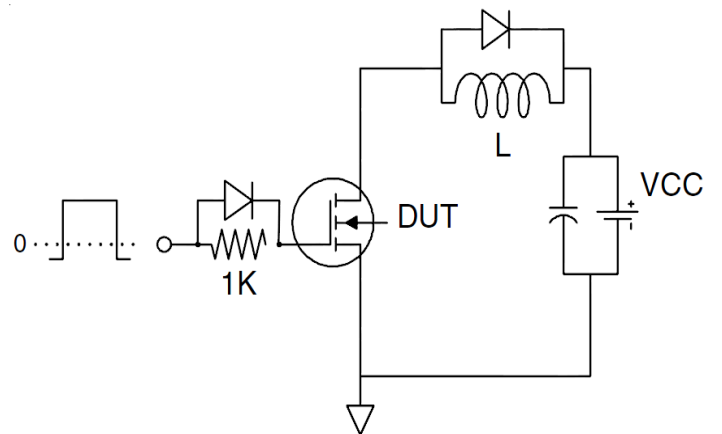
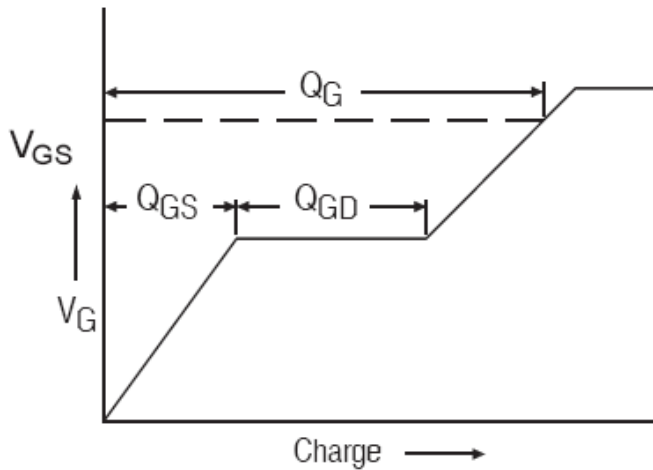
Notes 1. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 1.5\%$, $R_G=25\Omega$, Starting $T_J=25^{\circ}C$

Test Circuit

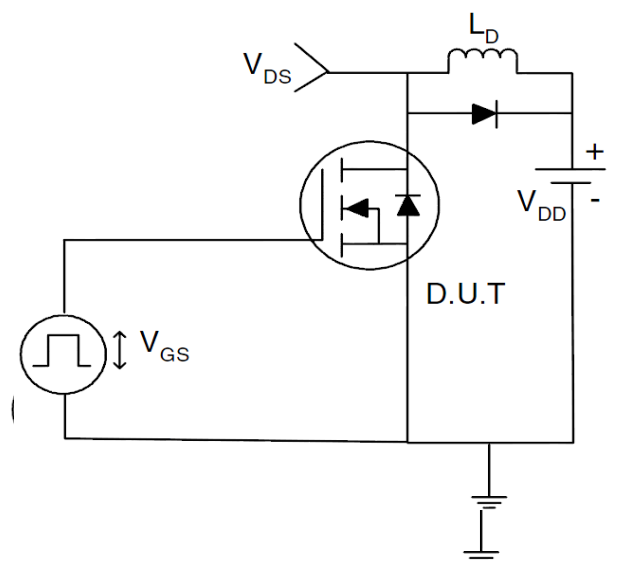
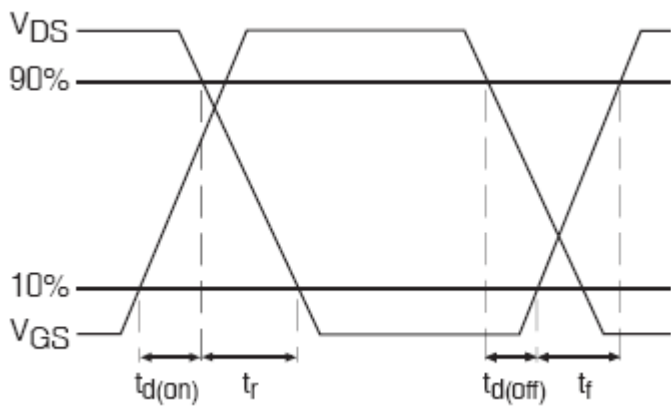
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. Output Characteristics

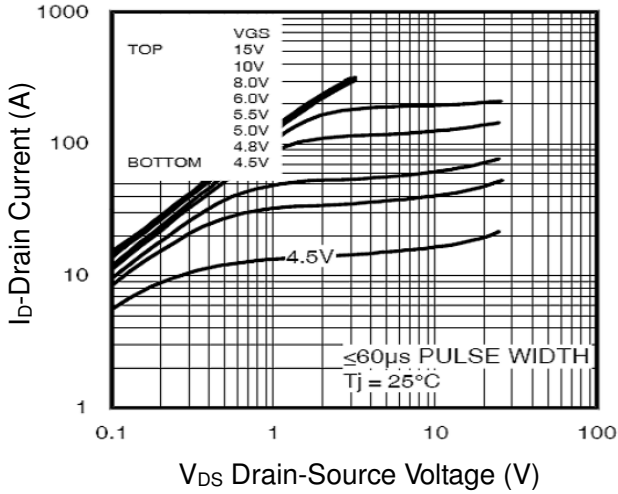


Figure2. Transfer Characteristics

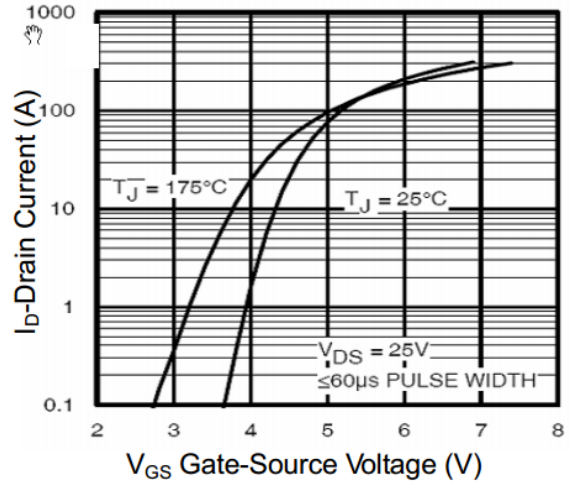


Figure3. BV_{DSS} vs Junction Temperature

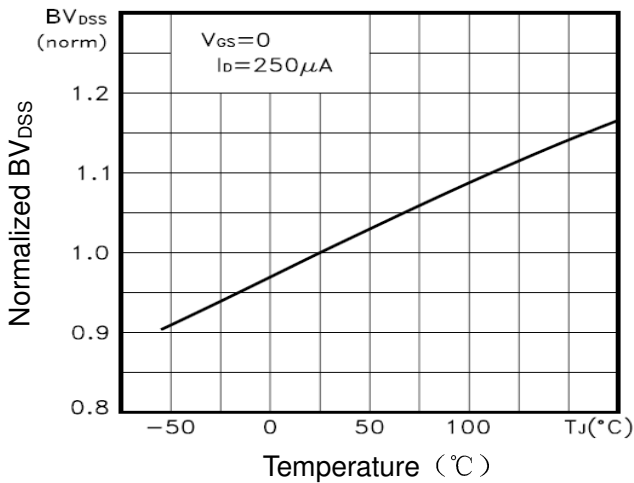


Figure4. ID vs Junction Temperature

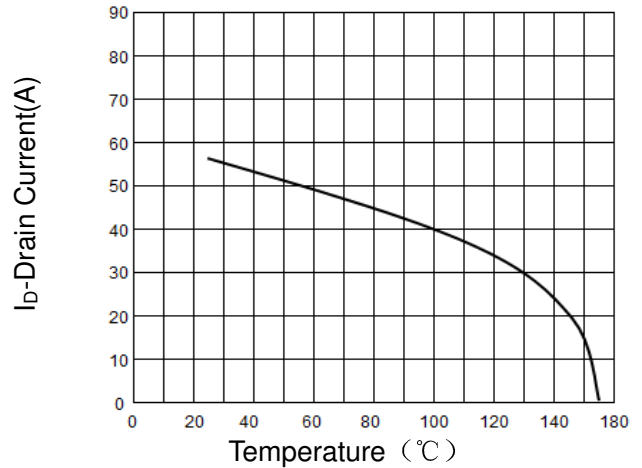


Figure5. VGS(th) vs Junction Temperature

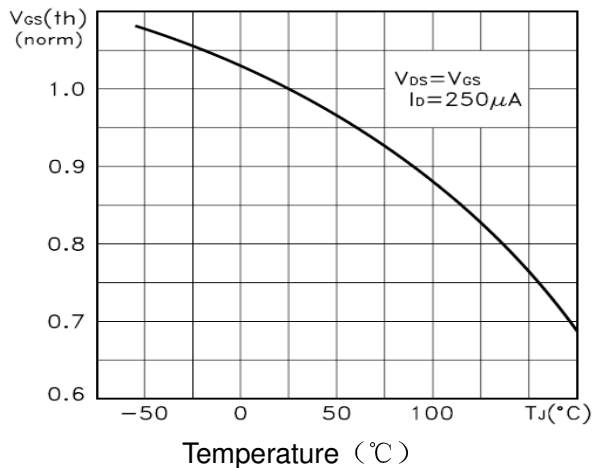


Figure6. R_{ds(on)} Vs Junction Temperature

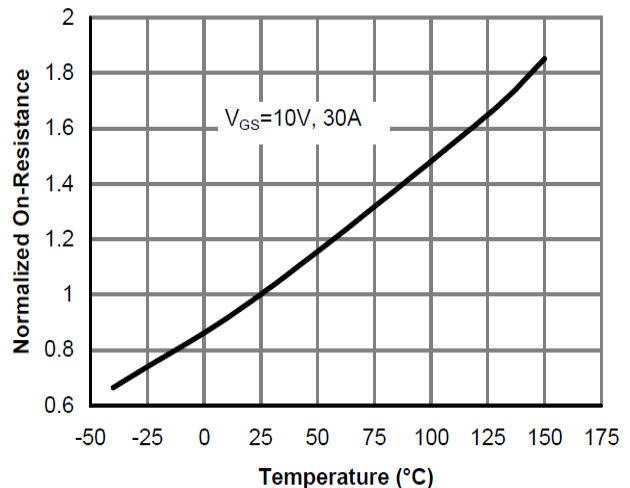


Figure7. Gate Charge

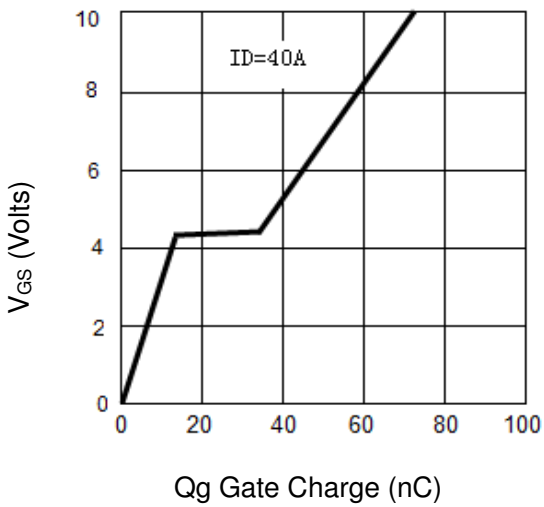


Figure8. Capacitance vs Vds

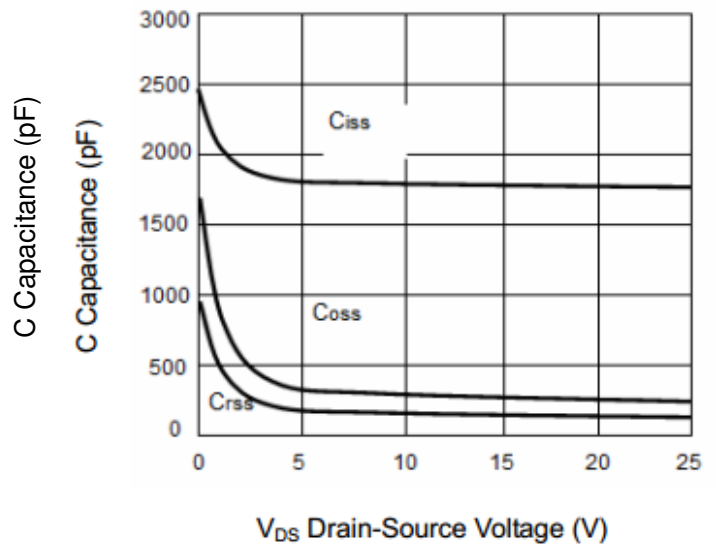


Figure9. Source- Drain Diode Forward

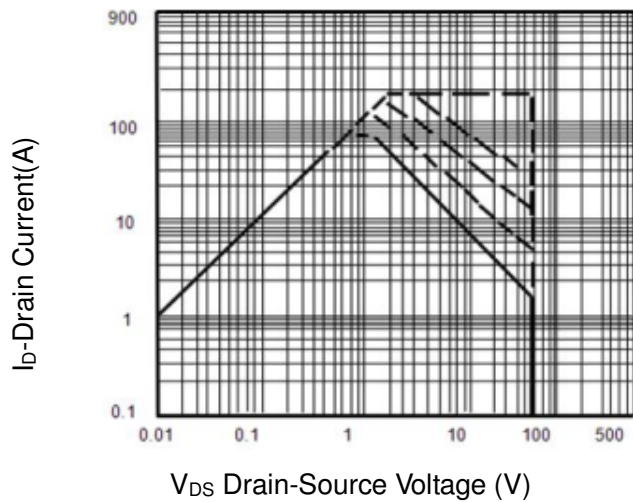
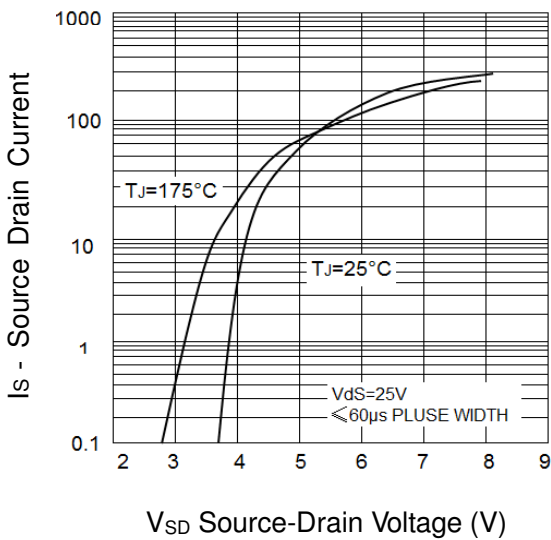
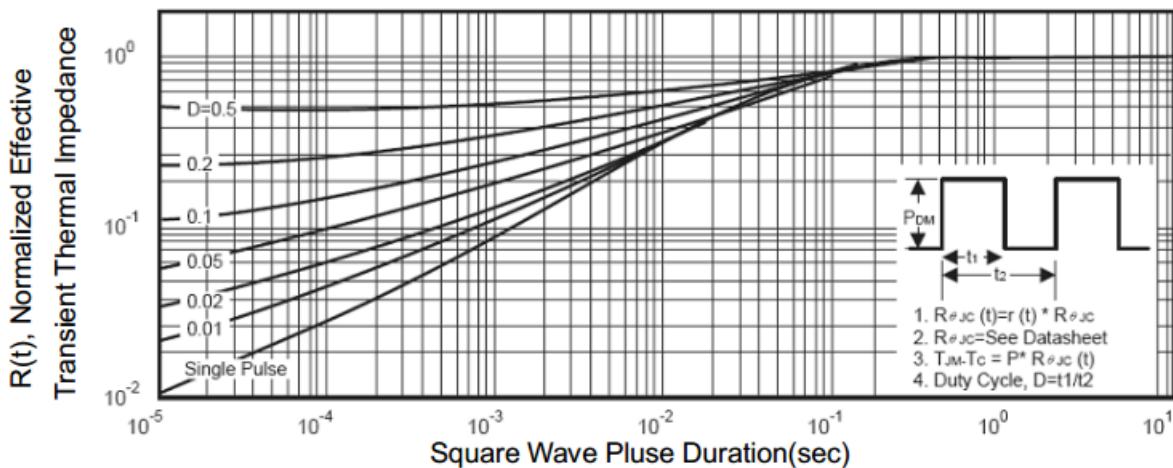
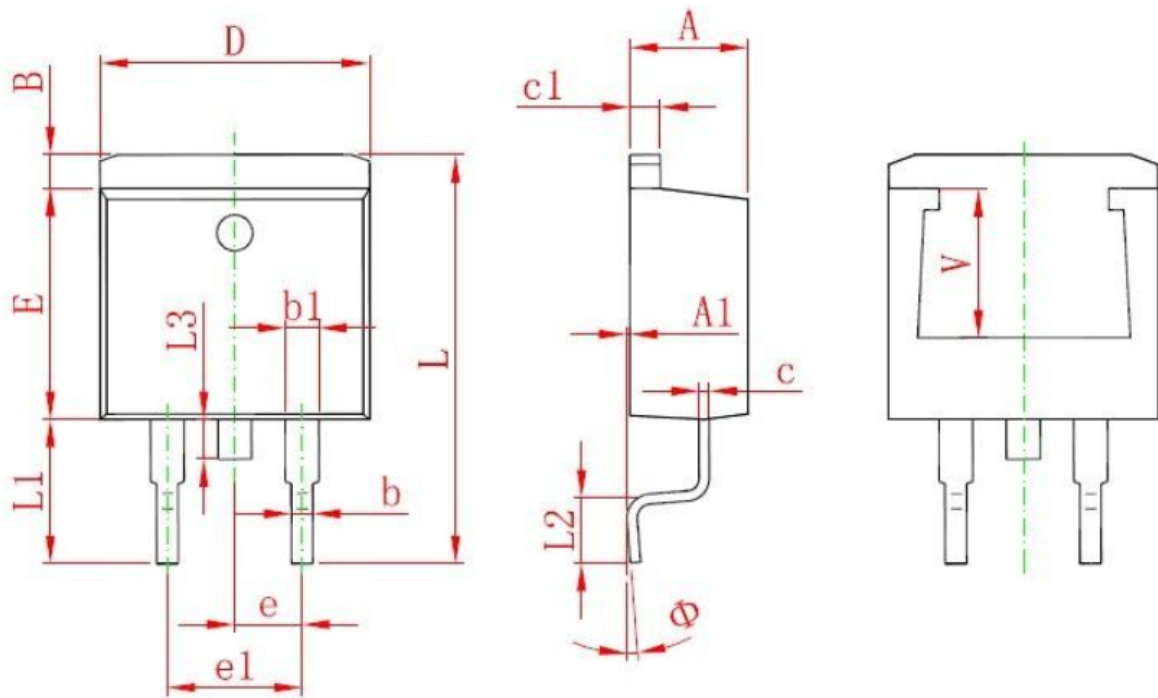


Figure11. Normalized Maximum Transient Thermal Impedance





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Ma
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF.		0.220REF.	
Φ	0°	8°	0°	8°